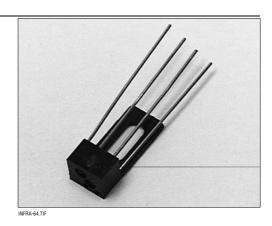
Reflective Sensor

FEATURES

- Choice of phototransistor or photodarlington output
- Focused for maximum response
- Wide operating temperature range (- 55°C to +100°C)



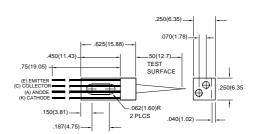
DESCRIPTION

The HOA2498 series consists of an infrared emitting diode and an NPN silicon phototransistor (HOA2498-001, - 002) or photodarlington (HOA2498-003), encased side- by- side on converging optical axes in a black thermoplastic housing. The detector responds to radiation from the IRED only when a reflective object passes within its field of view. The HOA2498 series employs metal can packaged components. For additional component information see SE1450, SD1440, and SD1410.

Housing material is polyester. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals $\pm 0.010(0.25)$ 2 plc decimals $\pm 0.020(0.51)$



DIM_039.ds4



Reflective Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	I _R			10	μΑ	V _R =3 V
DETECTOR Collector-Emitter Breakdown Voltage HOA2498-001, -002 HOA2498-003	V _(BR) ceo	30 15			٧	I _C =100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector Dark Current HOA2498-001, -002 HOA2498-003	Iceo			100 250	nA	V _{CE} =10 V I _F =0
COUPLED CHARACTERISTICS On-State Collector Current HOA2498-001 HOA2498-002 HOA2498-003	Ic(on)	0.04 0.16 2.0			mA	VcE=5 V IF=30 mA (1)
Collector-Emitter Saturation Voltage HOA2498-001 HOA2498-002 HOA2498-003	VCE(SAT)			0.4 0.4 1.1	V	I _F =30 mA ⁽¹⁾ I _C =5 μΑ I _C =20 μΑ I _C =250 μΑ
Rise And Fall Time HOA2498-001, -002 HOA2498-003	t _r , t _f		15 75		μѕ	V_{CC} =5 V, I _C =1 mA R_L =1000 Ω R_L =100 Ω

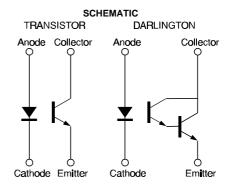
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted) Operating Temperature Range -55°C to 100°C Storage Temperature Range -55°C to 125°C Soldering Temperature (10 sec) 260°C

IR EMITTER

Power Dissipation 75 mW (1) Reverse Voltage 3 V 50 mA Continuous Forward Current

DETECTOR TRANS. DARLINGTON 30 V 15 V Collector-Emitter Voltage **Emitter-Collector Voltage** 5 V 5 V 75 mW ⁽¹⁾ 75 mW (1) Power Dissipation Collector DC Current 30 mA 30 mA



Honeywell reserves the right to make changes in order to improve design and supply the best products possible. Honeywell

Notes
1. Test surface is a front surface mirror (polished aluminum, 85% reflectance) located 0.50 in.(12.7 mm) from the front surface of the

Reflective Sensor

0.8

1.0

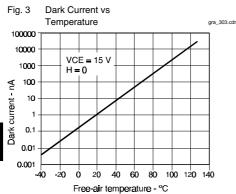
1.6

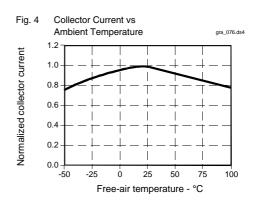
Forward voltage - V

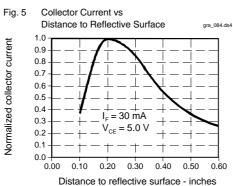
1.8

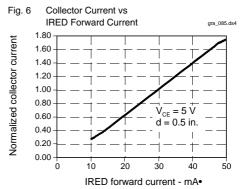
2.0

Fig. 2 Non-Saturated Switching Time vs Load Resistance gra_079.ds4 1000 ≡ı≡⊞ Response time - µs 100 Photodarlington = = = = Phototransistor ŦI#II# 10 100 1000 10000 Load resistance - Ohms









All Performance Curves Show Typical Values

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Reflective Sensor



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